K. Memory (Design & Process Technology) 분과

2017년 2월 14일 (화), 08:30-10:00 Room B (토파즈, 2층)

[TB1-K] Unconventional Approaches in Resistance Switching Memories

좌장: 손용훈(삼성전자), 강명곤(한국교통대학교)

| TB1-K-1 08:30-08:45 | Improving Resistive Switching Uniformity by Embedding Au Nanodots in the Pt/Ta ₂ O ₅ /HfO _{2-x} /TiN Structure |
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| | Young Jae Kwon, Jung Ho Yoon, Yu Min Kim, Dae Eun Kwon, Tae Hyung Park, Kyung Jin Yoon, Hae Jin Kim, Xing Long Shao and Cheol Seong Hwang Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University |
| TB1-K-2 08:45-09:00 | Investigation of Bipolar Resistive Switching Behaviors based on Solution Processed AlO _x Thin Film Using Microwave Irradiation |
| | Seung-Tae Kim and Won-Ju Cho Department of Electronic Materials Engineering, Kwangwoon University |
| TB1-K-3 09:00-09:15 | The Effect of Oxygen-Content in LaAlO ₃ Layer on the Synaptic Behavior of Pt/LaAlO ₃ /Nb:SrTiO ₃ Memristors for Neuromorphic Applications |
| | Jun Tae Jang ¹ , Daehyun Ko ¹ , Geumho Ahn ¹ , Hyery Yu ¹ , Yeon Soo Kim ² , Chansoo Yoon ² , Sangik Lee ² , Bae Ho Park ² , Sung-Jin Choi ¹ , Dong Myong Kim ¹ , and Dae Hwan Kim ¹ ¹ School of Electrical Engineering, Kookmin University, ² Department of Physics, Konkuk University |
| TB1-K-4 09:15-09:30 | The Influence of Oxygen-Content on the Synaptic Behavior of InGaZnO Memristors for Neuromorphic Applications |
| | Geumho Ahn, Jun Tae Jang, Daehyun Ko, Hyeri Yu, Sung-Jin Choi, Dong Myong Kim, and Dae Hwan Kim School of Electrical Engineering, Kookmin University |
| TB1-K-5 09:30-09:45 | Flexible Resistive Memory Array on Plastics via Laser Lift-off |
| | Seungjun Kim, Dohyun Kim, and Keon Jae Lee Department of Materials Science and Engineering, KAIST |
| TB1-K-6 09:45-10:00 | 열 변성 단백질을 이용한 비휘발성 스위칭 소자 |
| | Sookyung Kim, Sung Kyu Jang, Sumin Jeon, and Sungjoo Lee SKKU Advanced Institute of Nano Technology(SAINT), Sungkyungkwan University |